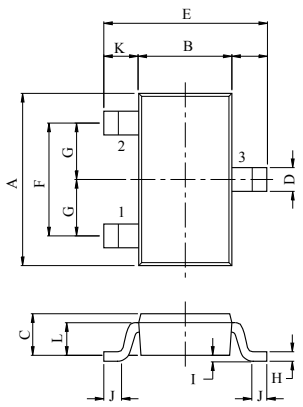
KTC3531T

EPITAXIAL PLANAR NPN TRANSISTOR

LOW FREQUENCY POWER AMP, CONVERTER
ELECTRONIC GOVERNOR APPLICATIONS

FEATURES

· Low Saturation Voltage
: $V_{CE(sat)}$=0.3V(Max.) at I_C=0.5A.
· Complementary to KTA1531T.



DIM	MILLIMETERS
A	2.9±0.2
B	1.6+0.2/-0.1
C	0.70±0.05
D	0.4±0.1
E	2.8+0.2/-0.3
F	1.9±0.2
G	0.95
H	0.16±0.05
I	0.00-0.10
J	0.25+0.25/-0.15
K	0.60
L	0.55

1. EMITTER
2. BASE
3. COLLECTOR

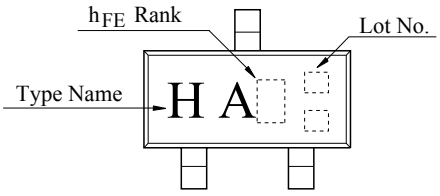
TSM

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Collector Power Dissipation	P_C *	0.9	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

* Package mounted on a ceramic board (600㎟×0.8㎜)

Marking

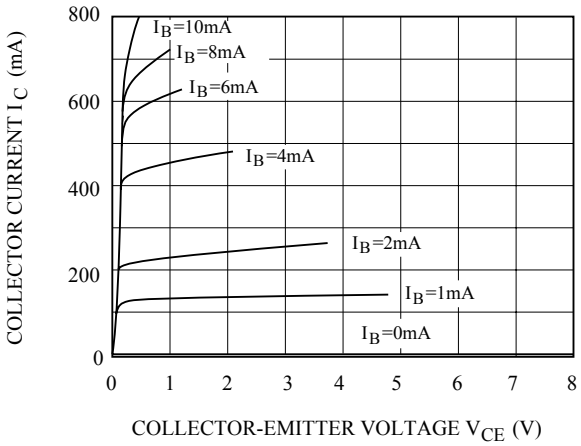


ELECTRICAL CHARACTERISTICS (Ta=25℃)

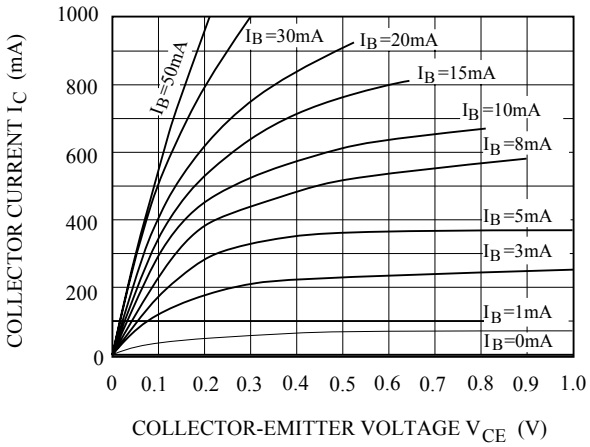
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=20V, I_E=0	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	0.1	μA
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=2V, I_C=50mA	120	-	400	
	h_{FE}(2)	V_{CE}=2V, I_C=1A(Pulse)	30	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA	-	0.1	0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=500mA, I_B=50mA	-	0.85	1.2	V
Transition Frequency	f_T	V_{CE}=10V, I_C=50mA	-	180	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	15	-	pF

Note : h_{FE} Classification Y:120～240, GR(G):200～400

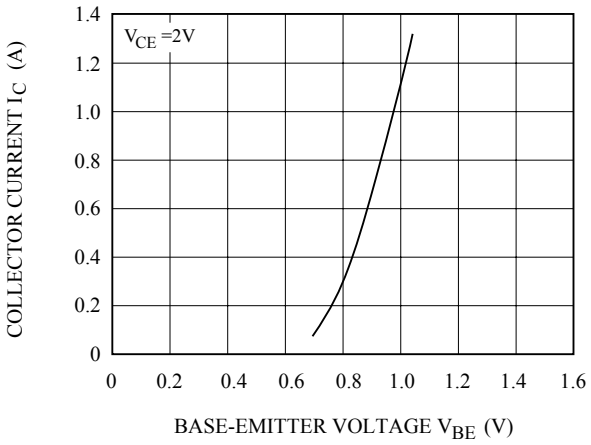
I_C - V_{CE}



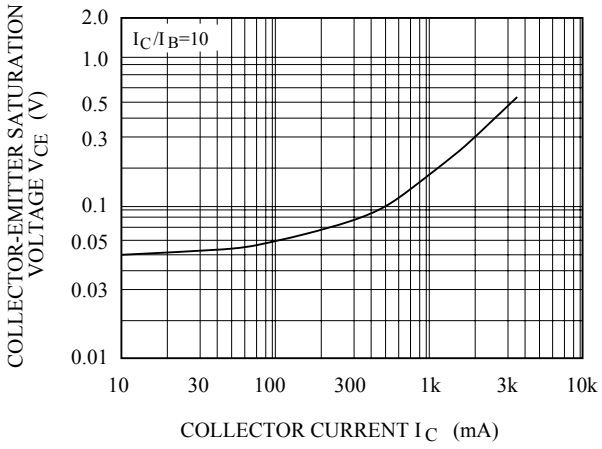
I_C - V_{CE}



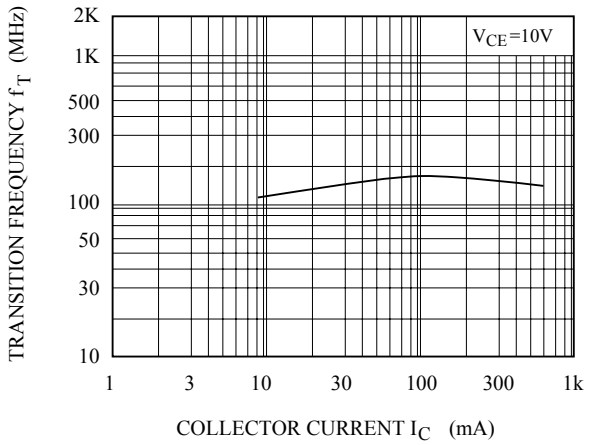
I_C - V_{BE}



$V_{CE(sat)}$ - I_C



f_T - I_C



h_{FE} - I_C

